

HA17902 Series

Quad Operational Amplifier

REJ03D0685-0100
(Previous: ADE-204-045)
Rev.1.00
Jun 15, 2005

Description

The HA17902 is an internal phase compensation quad operational amplifier that operates on a single-voltage power supply and is appropriate for use in a wide range of general-purpose control equipment.

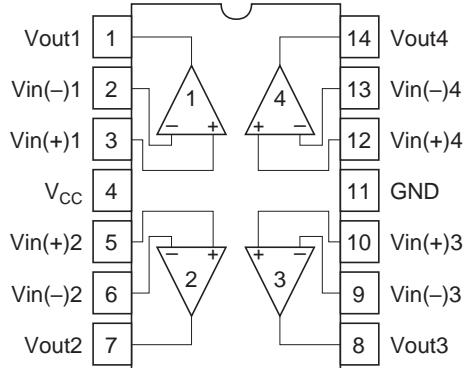
Features

- Wide usable power-supply voltage range and single-voltage supply operation
- Internal phase compensation
- Wide common-mode voltage range and operation for inputs close to the 0 level

Ordering Information

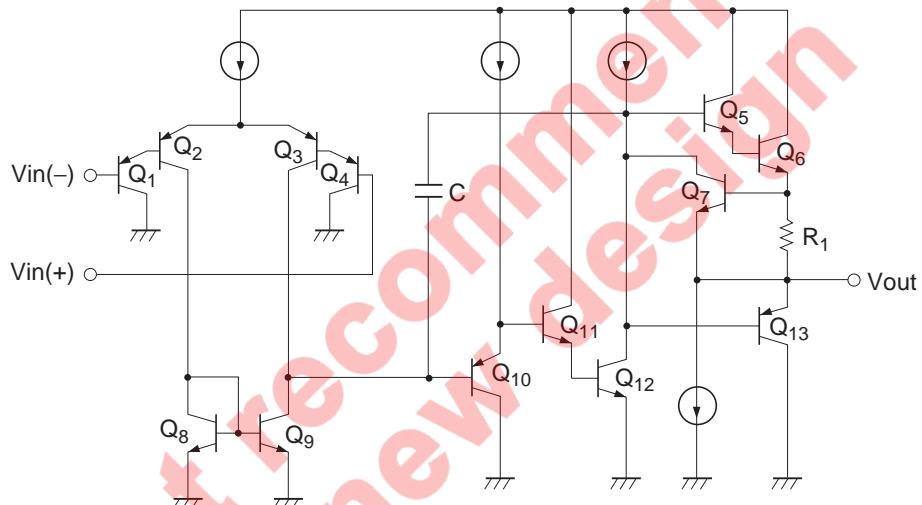
Type No.	Application	Package Code (Previous Code)
HA17902PJ	Car use	PRDP0014AB-A (DP-14)
HA17902FPJ		PRSP0014DF-B (FP-14DAV)
HA17902FPK		PRSP0014DF-B (FP-14DAV)

Pin Arrangement



(Top view)

Circuit Structure (1/4)



Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	HA17902PJ	HA17902 FPJ	HA17902FPK	Unit
Power supply voltage	V _{CC}	28	28	28	V
Sink current	I _{O sink}	50	50	25	mA
Allowable power dissipation	P _T	625* ¹	625* ²	625* ²	mW
Common-mode input voltage	V _{CM}	-0.3 to V _{CC}	-0.3 to V _{CC}	-0.3 to V _{CC}	V
Differential-mode input voltage	V _{in(diff)}	±V _{CC}	±V _{CC}	±V _{CC}	V
Operating temperature	T _{opr}	-40 to +85	-40 to +85	-40 to +125	°C
Storage temperature	T _{stg}	-55 to +125	-55 to +125	-55 to +150	°C

Notes: 1. These are the allowable values up to Ta = 50°C. Derate by 8.3mW/°C above that temperature.

2. See notes on SOP Package Usage in Reliability section.

Electrical Characteristics 1(V_{CC} = + 15V, Ta = 25°C)

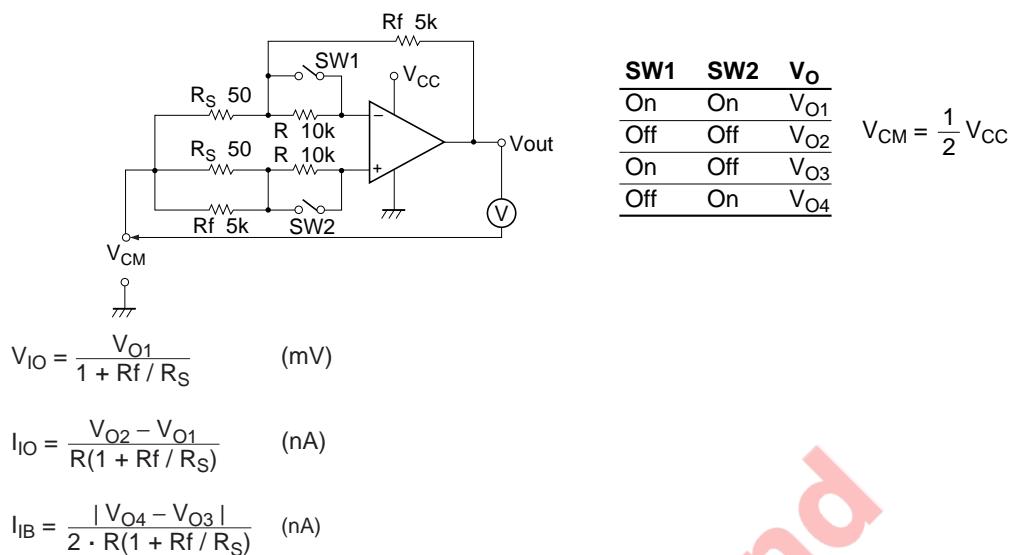
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input offset voltage	V _{IO}	—	3	8	mV	V _{CM} = 7.5V, R _S = 50Ω, R _f = 5kΩ
Input offset current	I _{IO}	—	5	50	nA	I _{IO} = I _{I⁻} - I _{I⁺} , V _{CM} = 7.5V
Input bias current	I _{IB}	—	30	500	nA	V _{CM} = 7.5V
Power-supply rejection ratio	PSRR	—	93	—	dB	f = 100Hz, R _S = 1kΩ, R _f = 100kΩ
Voltage gain	A _{VD}	75	90	—	dB	R _S = 1kΩ, R _f = 100kΩ, R _L = ∞
Common-mode rejection ratio	CMR	—	80	—	dB	R _S = 50Ω, R _f = 5kΩ
Common-mode input voltage range	V _{CM}	-0.3	—	13.5	V	R _S = 1kΩ, R _f = 100kΩ, f = 100Hz
Maximum output voltage amplitude	V _{OP-P}	—	13.6	—	V	f = 100Hz, R _S = 1kΩ, R _f = 100kΩ, R _L = 20kΩ
Output voltage	V _{OH1}	13.2	13.6	—	V	I _{OH} = -1mA
	V _{OH2}	12	13.3	—	V	I _{OH} = -10mA
	V _{OL1}	—	0.8	1	V	I _{OL} = 1mA
	V _{OL2}	—	1.1	1.8	V	I _{OL} = 10mA
Output source current	I _{O source}	15	—	—	mA	V _{OH} = 10V
Output sink current	I _{O sink}	3	9	—	mA	V _{OL} = 1V
Supply current	I _{CC}	—	0.8	2	mA	V _{in} = GND, R _L = ∞
Slew rate	SR	—	0.19	—	V/μs	f = 1.5kHz, V _{CM} = 7.5V, R _L = ∞
Channel separation	CS	—	120	—	dB	f = 1kHz

Electrical Characteristics 2(V_{CC} = + 15V, Ta = - 40 to 125°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Input offset voltage	V _{IO}	—	—	8	mV	V _{CM} = 7.5V, R _S = 50Ω, R _f = 5kΩ
Input offset current	I _{IO}	—	—	200	nA	V _{CM} = 7.5V, I _{IO} = I _{I⁻} - I _{I⁺}
Input bias current	I _{IB}	—	—	500	nA	V _{CM} = 7.5V
Common-mode input voltage range	V _{CM}	0	—	13.0	V	R _S = 1kΩ, R _f = 100kΩ, f = 100Hz
Output voltage	V _{OH}	13.0	—	—	V	I _{OH} = -1mA
	V _{OL}	—	—	1.3	V	I _{OL} = 1mA
Supply current	I _{CC}	—	—	4	mA	V _{in} = GND, R _L = ∞

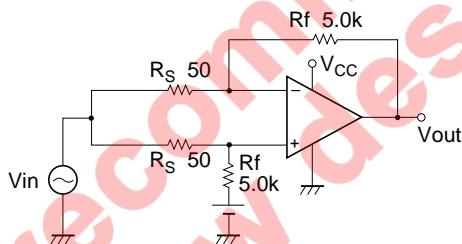
Test Circuits

1. Input offset voltage (V_{IO}), input offset current (I_{IO}), and Input bias current (I_{IB}) test circuit

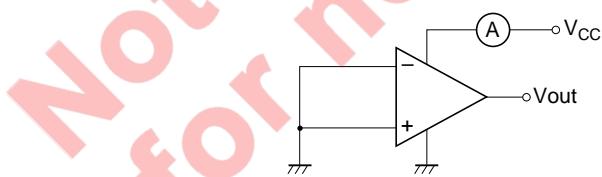


2. Common-mode rejection ratio (CMR) test circuit

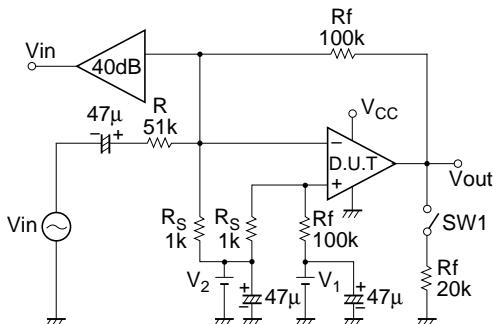
$$\text{CMR} = 20 \log \frac{V_{IN} \cdot R_f}{V_o \cdot R_S} \quad (\text{dB})$$



3. Supply current (I_{CC}) test circuit



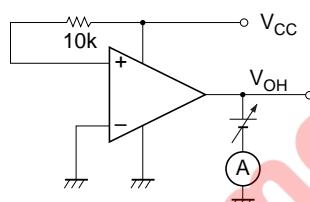
4. Voltage gain (A_{VD}), slew rate (SR), common-mode input voltage range (V_{CM}), and maximum output voltage amplitude (V_{OP-P}) test circuit.



(1) A_{VD} : $R_S = 1\text{k}\Omega$, $R_f = 100\text{k}\Omega$, $R_L = \infty$, $V_1 = V_2 = 1/2 V_{CC}$

$$A_{VD} = 20 \log \frac{V_O}{V_{IN}} + 40 \quad (\text{dB})$$

(2) SR: $f = 1.5\text{kHz}$, $R_L = \infty$, $V_1 = V_2 = 1/2 V_{CC}$



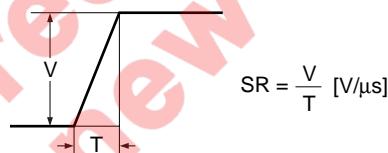
(3) V_{CM} : $R_S = 1\text{k}\Omega$, $R_f = 100\text{k}\Omega$, $f = 100\text{Hz}$, $V_1 = 1/2 V_{CC}$, $R_L = \infty$,

and the value of V_2 just slightly prior to the point where the output waveform changes.

(4) V_{OP-P} : $R_S = 1\text{k}\Omega$, $R_f = 100\text{k}\Omega$, $R_L = 20\text{k}\Omega$, $f = 100\text{Hz}$, $V_{OP-P} = V_{OH} \leftrightarrow V_{OL}$ [V_{P-P}]

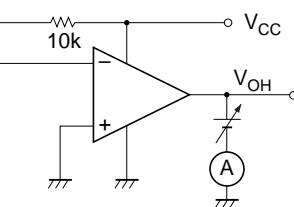
5. Output source current (Iosource) test circuit

Io source: $V_{OH} = 10\text{V}$

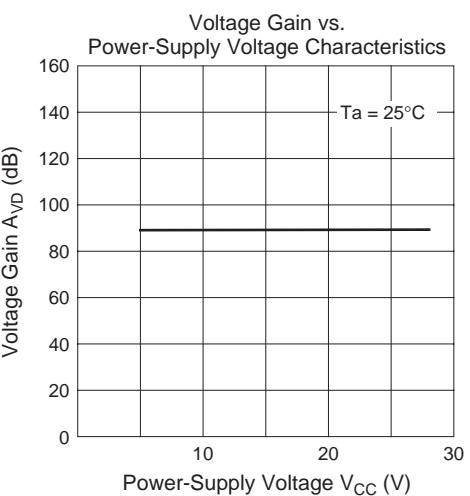
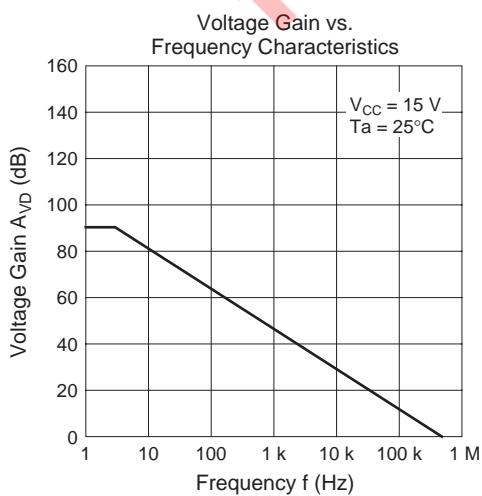
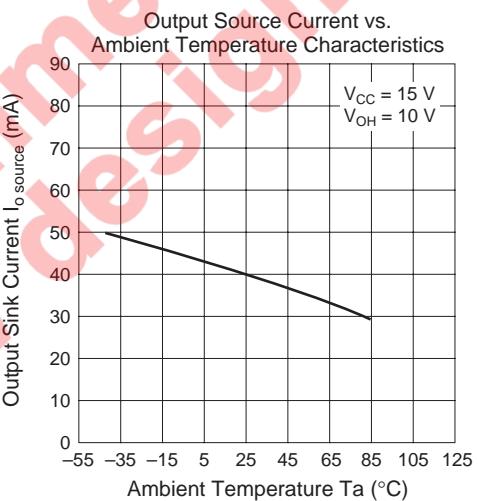
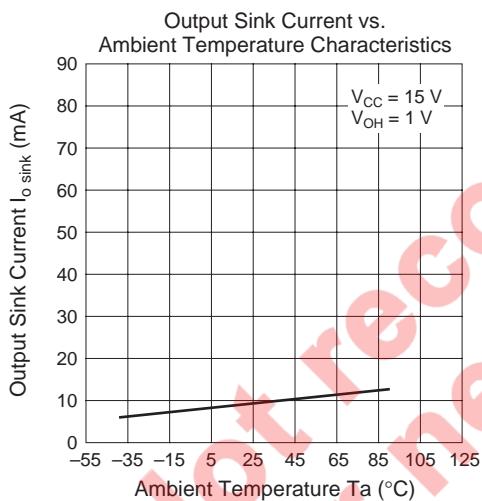
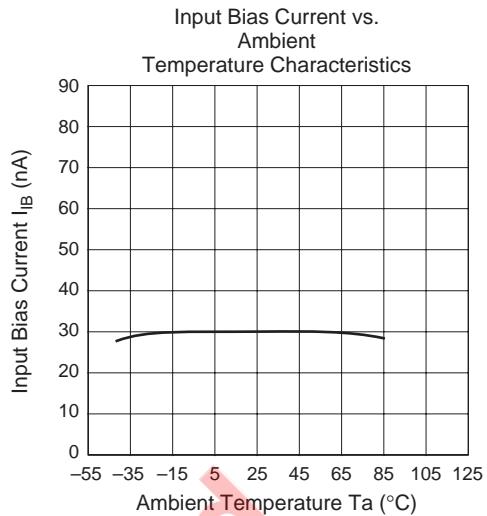
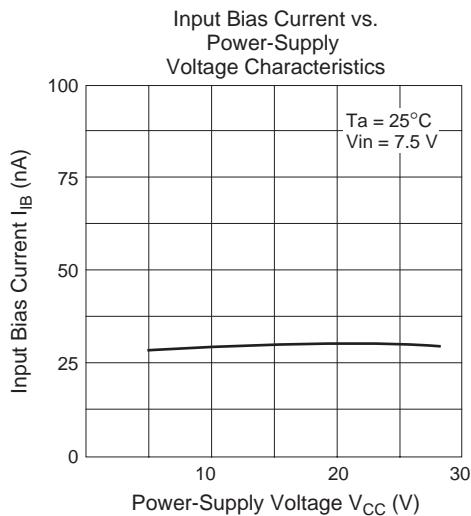


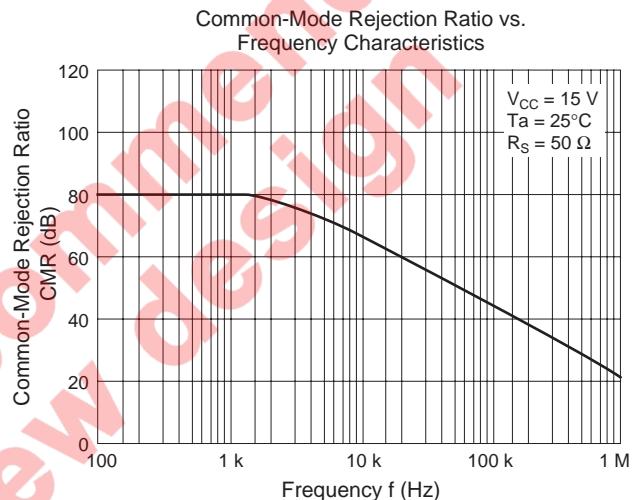
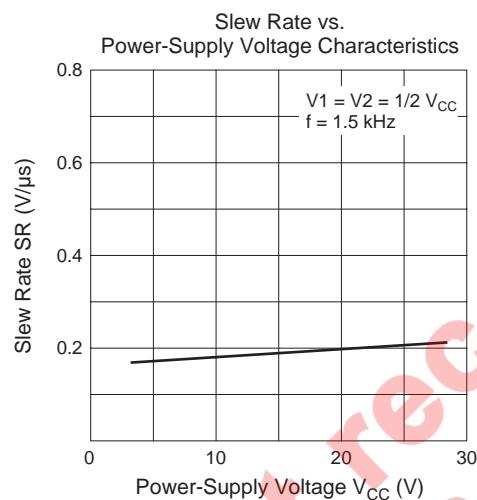
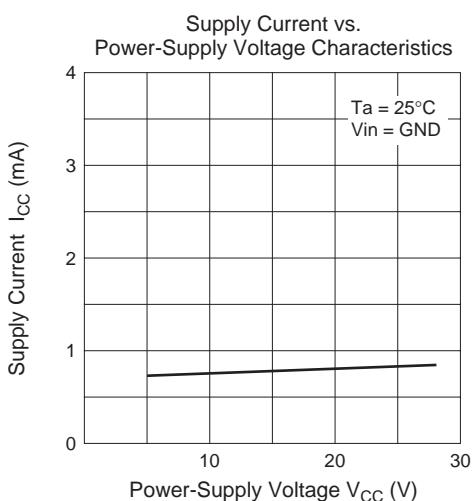
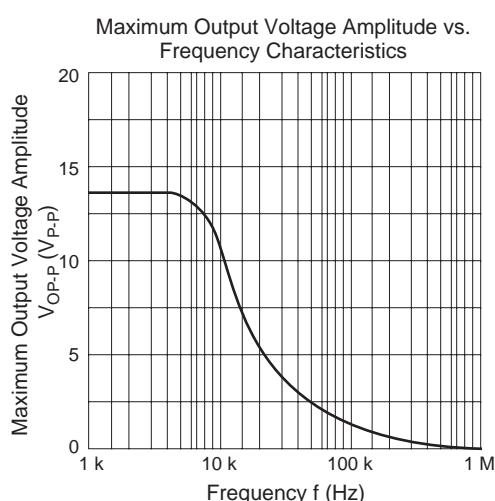
6. Output sink current (Iosink) test circuit

Io sink: $V_{OL} = 1\text{V}$



Characteristics Curve





HA17902 Application Examples

The HA17902 is a quad operational amplifier, and consists of four operational amplifier circuits and one bias current circuit. It features single-voltage power supply operation, internal phase compensation, a wide zero-cross bandwidth, a low input bias current, and a high open-loop gain. Thus the HA17902 can be used in a wide range of applications. This section describes several applications using the HA17902.

1. Noninverting Amplifier

Figure 1 shows the circuit diagram for a noninverting amplifier. The voltage gain of this amplifier is given by the following formula.

$$\frac{V_{out}}{V_{in}} = 1 + \frac{R_2}{R_1}$$

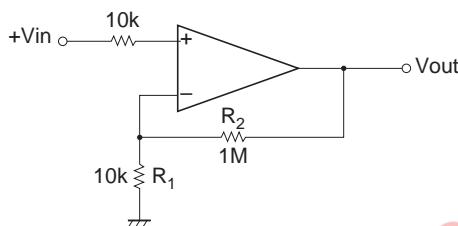


Figure 1 Noninverting Amplifier

2. Summing Amplifier

Since the circuit shown in figure 2 applies $+V_1$ and $+V_2$ to the noninverting input and $+V_3$ and $+V_4$ to the inverting input, the total output will be $V_{out} = V_1 + V_2 - V_3 - V_4$.

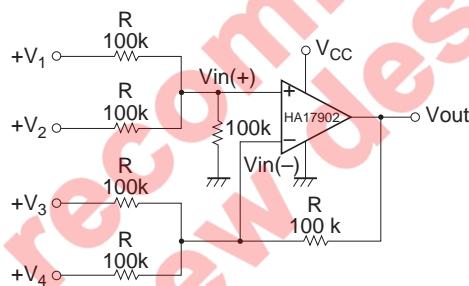


Figure 2 Summing Amplifier

3. High Input Impedance DC Differential Amplifier

The circuit shown in figure 3 is a high input impedance DC differential amplifier. This circuit's common-mode rejection ratio (CMR) depends on the matching between the R_1/R_2 and R_4/R_3 resistance ratios. This amplifier's output is given by the following formula.

$$V_{out} = \left(1 + \frac{R_4}{R_3}\right) (V_2 - V_1)$$

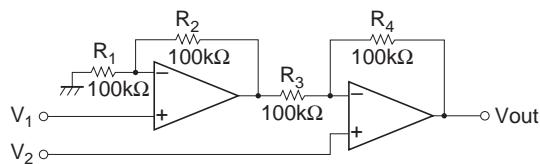


Figure 3 High Input Impedance DC Differential Amplifier

4. Voltage Controlled Oscillator

Figure 4 shows an oscillator circuit in which the amplifier A_1 is an integrator, the amplifier A_2 is a comparator, and transistor Q_1 operates as a switch that controls the oscillator frequency. If the output V_{out1} is at the low level, this will cut off transistor Q_1 and cause the A_1 inverting input to go to a higher potential than the noninverting input. Therefore, A_1 will integrate this negative input state and its output level will decrease. When the A_1 integrator output becomes lower than the A_2 comparator noninverting input level ($V_{CC}/2$) the comparator output goes high. This turns on transistor Q_1 causing the integrator to integrate a positive input state and for its output to increase. This operation generates a square wave on V_{out1} and a triangular wave on V_{out2} .

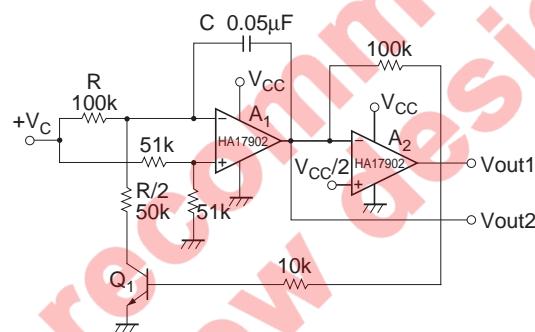


Figure 4 Voltage Controlled Oscillator

Package Dimensions

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-DIP14-6.3x19.2-2.54	PRDP0014AB-A	DP-14	0.97g

Dimensions shown in the top view:

- Width (D): 19.2 mm
- Height (E): 6.3 mm
- Lead thickness (A): 5.06 mm
- Lead height (A1): 0.51 mm
- Lead length (L): 2.54 mm
- Lead width (bP): 0.38 mm
- Lead spacing (b3): 1.3 mm
- Lead pitch (c): 0.20 mm
- Lead angle (theta): 15°
- Lead height (e): 2.29 mm
- Lead thickness (Z): 2.79 mm

Dimensions shown in the side view:

- Width (D): 19.2 mm
- Height (E): 6.3 mm
- Lead thickness (A): 5.06 mm
- Lead height (A1): 0.51 mm
- Lead length (L): 2.54 mm
- Lead width (bP): 0.38 mm
- Lead spacing (b3): 1.3 mm
- Lead pitch (c): 0.20 mm
- Lead angle (theta): 15°
- Lead height (e): 2.29 mm
- Lead thickness (Z): 2.79 mm

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
e ₁	—	7.62	—
D	—	19.2	20.32
E	—	6.3	7.4
A	—	—	5.06
A ₁	0.51	—	—
b _P	0.38	0.48	0.58
b ₃	—	1.3	—
c	0.20	0.25	0.35
θ	0°	—	15°
Z	—	—	2.79
L	2.54	—	—

JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-SOP14-5.5x10.06-1.27	PRSP0014DF-B	FP-14DAV	0.23g

Dimensions shown in the top view:

- Width (D): 10.06 mm
- Height (E): 5.50 mm
- Lead thickness (A): 2.20 mm
- Lead height (A1): 0.10 mm
- Lead width (bP): 0.40 mm
- Lead spacing (b3): 0.34 mm
- Lead angle (theta): 8°
- Lead height (e): 1.27 mm
- Lead thickness (Z): 0.12 mm
- Lead width (c): 0.20 mm
- Lead pitch (A): 0.50 mm
- Lead length (L): 1.15 mm

Dimensions shown in the side view:

- Width (D): 10.06 mm
- Height (E): 5.50 mm
- Lead thickness (A): 2.20 mm
- Lead height (A1): 0.10 mm
- Lead width (bP): 0.40 mm
- Lead spacing (b3): 0.34 mm
- Lead angle (theta): 8°
- Lead height (e): 1.27 mm
- Lead thickness (Z): 0.12 mm
- Lead width (c): 0.20 mm
- Lead pitch (A): 0.50 mm
- Lead length (L): 1.15 mm

Dimensions shown in the cross-sectional view:

- Width (D): 10.06 mm
- Height (E): 5.50 mm
- Lead thickness (A): 2.20 mm
- Lead height (A1): 0.10 mm
- Lead width (bP): 0.40 mm
- Lead spacing (b3): 0.34 mm
- Lead angle (theta): 8°
- Lead height (e): 1.27 mm
- Lead thickness (Z): 0.12 mm
- Lead width (c): 0.20 mm
- Lead pitch (A): 0.50 mm
- Lead length (L): 1.15 mm

NOTE:
1. DIMENSIONS^{*1} (Nom) AND^{*2} (Max)
DO NOT INCLUDE MOLD FLASH.
2. DIMENSION^{*3} DOES NOT
INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	—	10.06	10.5
E	—	5.50	—
A ₂	—	—	—
A ₁	0.00	0.10	0.20
A	—	—	2.20
b _P	0.34	0.40	0.46
b ₁	—	—	—
c	0.15	0.20	0.25
c ₁	—	—	—
θ	0°	—	8°
H _E	7.50	7.80	8.00
[e]	—	1.27	—
x	—	—	0.12
y	—	—	0.15
Z	—	—	1.42
L	0.50	0.70	0.90
L ₁	—	1.15	—

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